

Pavel Yu Bokov

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Electroreflectance spectra of InGaN/AlGaIn/GaN quantum-well heterostructures. Semiconductors, 2007, 41, 1060-1066.	0.5	9
2	Interference effects in the electroreflectance and electroluminescence spectra of InGaN/AlGaIn/GaN light-emitting-diode heterostructures. Semiconductors, 2010, 44, 1090-1095.	0.5	8
3	Electrical and optical properties of near-surface AlGaAs/InGaAs/AlGaAs quantum wells with different quantum-well depths. Semiconductors, 2013, 47, 1203-1208.	0.5	8
4	Study of the effects of size quantization in coupled $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ as quantum wells by means of photorefectance spectroscopy. Optics and Spectroscopy (English Translation of Optika i Spektroskopiya) 2007, 10, 100-105.	0.5	10
5	Unintentional indium incorporation into barriers of InGaN/GaN multiple quantum wells studied by photorelectance and photoluminescence excitation spectroscopy. Journal of Applied Physics, 2016, 120, .	2.5	5
6	Photorefection studies of band offsets at the heterojunction in strained short-period GaAs/GaAsP superlattices. Semiconductors, 2004, 38, 1384-1389.	0.5	4
7	Interband optical transitions in GaAs modulation-doped quantum wells: photorelectance experiment and self-consistent calculations. Semiconductor Science and Technology, 2006, 21, 462-466.	2.0	4
8	Piezoelectric field compensation in the InGaIn quantum wells of GaN/InGaIn/AlGaIn LEDs structures: electroreflectance experiment. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1863-1865.	0.8	3
9	The difference between reflectance and electroreflectance spectra of AlGaIn/GaN/InGaIn LED structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 818-821.	0.8	3
10	Photorefection Studies of the Dopant Activation in InP Implanted with Be ⁺ Ions. Semiconductors, 2005, 39, 174.	0.5	2
11	Determination of the carrier concentration in doped n-GaAs layers by Raman and light reflection spectroscopies. Optics and Spectroscopy (English Translation of Optika i Spektroskopiya), 2007, 102, 712-716.	0.6	2
12	Photorelectance spectroscopy of delta-doped GaAs layers. Inorganic Materials, 2011, 47, 455-458.	0.8	2
13	Impact of AlN Spacer on Metal-Semiconductor-Metal Pt-InAlGaIn/GaN Heterostructures for Ultraviolet Detection. Japanese Journal of Applied Physics, 2013, 52, 08JK04.	1.5	2
14	Study of built-in electric field in active region of GaN/InGaIn/AlGaInLEDs by electroreflectance spectroscopy. Solid-State Electronics, 2017, 130, 45-48.	1.4	2
15	Electroreflectance diagnostics of InGaIn/AlGaIn/GaN based LEDs structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2852-2854.	0.8	1
16	Photorelectance spectroscopy of electron-hole states in a graded-width GaAs/InGaAs/GaAs quantum well. Semiconductors, 2011, 45, 320-324.	0.5	1
17	Characterization of the spatial inhomogeneity of heterointerfaces in GaAs/AlGaAs quantum wells by photorelectance spectroscopy. Semiconductors, 2015, 49, 1202-1206.	0.5	1
18	Electroreflectance spectra from multiple InGaIn/GaN quantum wells in the nonuniform electric field of a p-n junction. Semiconductors, 2017, 51, 189-192.	0.5	1

#	ARTICLE	IF	CITATIONS
19	Raman scattering in InP doped by Be ⁺ -ion implantation. Semiconductors, 2017, 51, 168-172.	0.5	1
20	Investigation of electronic transitions in coupled-quantum-well structures with a built-in electric field by photoreflectance spectroscopy. Semiconductors, 2003, 37, 77-81.	0.5	0
21	Electroreflectance Spectra of InGaN/AlGaIn/GaN p-n-Heterostructures. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
22	A Role of the Built-in Piezoelectric Field in InGaN/AlGaIn/GaN Multiple Quantum Wells in the Electroreflectance Experiments. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
23	Photoreflectance study of plasma-etched semi-insulating GaAs substrates treated. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 941-943.	0.6	0
24	Linear Electro-Optic Effect in Electroreflectance Spectra of AlGaIn/InGaIn/GaN Light Emitting Diodes Structures. Japanese Journal of Applied Physics, 2013, 52, 08JK11.	1.5	0